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CLAIMS 1 – 5 (CANCELLED)

6. (ORIGINAL) A semiconductor laser comprising:
a light emission function layer stack including a cladding layer and an active layer formed on one plane of a translucent substrate;
two electrodes having different polarities, which are provided on said light emission function layer stack side; and
a light leakage preventive film formed on the other plane of said translucent substrate.
7. (ORIGINAL) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a light absorbing film.
8. (ORIGINAL) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a light reflecting film.
9. (ORIGINAL) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a dielectric film.

10. (ORIGINAL) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a metal film.

11. (ORIGINAL) A semiconductor laser according to claim 6, wherein a thickness of said light leakage preventive film is set to a value of $\lambda/4n$ where λ is a wavelength of light emitted from said light emission function layer stack and n is a refractive index of said light leakage preventive film.

12. (ORIGINAL) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a multi-layer film of dielectrics, and a thickness of each layer of said multi-layer film of dielectrics is set to a value of $\lambda/4n$ where λ is a wavelength of light emitted from said light emission function layer stack and n is a refractive index of said light leakage preventive film.

13. (ORIGINAL) A semiconductor laser according to claim 6, wherein each layer of said light emission function layer stack is made from a GaN base semiconductor.

14. (ORIGINAL) A semiconductor laser according to claim 6, wherein said translucent substrate is made from sapphire.

15. (ORIGINAL) A semiconductor laser according to claim 6, wherein said translucent substrate is made from GaN.

CLAIMS 16 – 22 (CANCELLED)